

PHASE EDGE PHASE SHIFT MASK ENFORCING A WIDTH OF A FIELD GATE IMAGE AND FABRICATION METHOD THEREOF

ABSTRACT

5 A phase edge phase shift mask and a fabrication method thereof for enforcing a width of a field gate image located on a field region, which is weakened by a two exposure process, by using a phase shift mask and a trim mask on a semiconductor substrate, and enforcing a width of the field gate image to maximize a current driving capability of the semiconductor device.